Table 1

Element	H <sub>0</sub> (Oe)	т <sub>с</sub> (°К)	θ <sub>D</sub> (°K)	γ exp (mJ/K <sup>2</sup> mol)	γcalc (mJ/K <sup>2</sup> mol)
GaI	59.3	1.08	317	0.598 [10]	1.02
GaII	620	6.24	200 [2]	1.63	0.92
Al	103	1.17	423	1.36 [10]	0.90
In	293	3.39	108	1.70 [10]	1.23

1 illustrate the relationship between Al, GaII and In.

In addition the question whether the change of the electron-phonon coupling constant or the increase in the density of states is responsible for both the high  $T_{\rm C}$  and the high  $\gamma$  of GaII, compared with GaI, can be answered. We may do this by using an expression for  $T_{\rm C}$  given by Jensen and Maita [5] and by McMillan [6]. Moreover we use an expression for  $\gamma$  due to Migdal [7].

$$T_{\rm c} = 0.69 \; \theta_{\rm D} \; \exp\{-(1 + \lambda)/(\lambda - \mu^*)\}$$
 (2)

$$\gamma \propto N(E_{\rm F})(1+\lambda)$$
 (3)

Here  $\lambda$  denotes the electron-phonon coupling constant,  $\mu^*$  is the effective Coulomb interaction and  $\theta_D$  is the Debye temperature.  $N(E_F)$  is the band structure density of states at the Fermi surface.  $\mu^*$  is taken to be 0.10, a value which has recently been confirmed by isotope effect measurements [8]. Assuming  $\lambda = N(E_F) \cdot V_{Dh}$  it turns out that  $V_{Dh}$ , the electron-phonon interaction coefficient, is decreased by going from GaI to GaII, while the density of states at the Fermi surface is increased by a factor of 2.3.

According to Ziman [9] we may also write

$$\lambda \approx C^2/M \,\theta_{\rm D}^2 \tag{4}$$

where M is the atomic mass and C is a measure

for the rigid-ion potential in the electron-phonon interaction. The change from GaI to GaII decrease  $C^2$  by a factor of about 1.4. It may be, however, that the uncertainty in  $\theta_D$  in the high pressure phase [2] is too large to make any reliable conclusions.

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